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May 2013

# TIL111M, TIL117M, MOC8100M General Purpose 6-Pin Phototransistor Optocouplers

#### **Features**

- UL Recognized (File # E90700)
- VDE Recognized (File #102497 for white package)Add Option V (e.g., TIL111VM)

#### **Applications**

- Power Supply Regulators
- Digital Logic Inputs
- Microprocessor Inputs
- Appliance Sensor Systems
- Industrial Controls

#### **General Description**

The MOC8100M, TIL111M, and TIL117M optocouplers consist of a gallium arsenide infrared emitting diode driving a silicon phototransistor in a 6-pin dual in-line package.

#### **Schematic**

# ANODE 1 0 6 BASE CATHODE 2 0 5 COLLECTOR NC 3 0 4 EMITTER

Figure 1. Schematic

#### **Package Outlines**

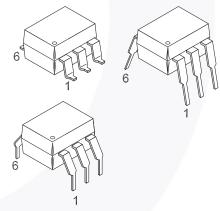


Figure 2. Package Outlines

#### **Safety and Insulation Ratings**

As per IEC60747-5-2. This optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Symbol	Parameter	Min.	Тур.	Max.	Unit
	Installation Classifications per DIN VDE 0110/1.89 Table 1				
	For Rated Mains Voltage < 150 V <sub>RMS</sub>		I–IV		
	For Rated Mains Voltage < 300 V <sub>RMS</sub>		I–IV		
	Climatic Classification		55/100/21		
	Pollution Degree (DIN VDE 0110/1.89)		2		
CTI	Comparative Tracking Index	175			
V <sub>PR</sub>	Input to Output Test Voltage, Method b, $V_{IORM} \times 1.875 = V_{PR}$ , 100% Production Test with $t_m = 1$ s, Partial Discharge < 5 pC	1594			
	Input to Output Test Voltage, Method a, $V_{IORM} \times 1.5 = V_{PR}$ , Type and Sample Test with $t_m = 60$ s, Partial Discharge < 5 pC	1275			
V <sub>IORM</sub>	Maximum Working Insulation Voltage	850			V <sub>peak</sub>
V <sub>IOTM</sub>	Highest Allowable Over Voltage	6000			V <sub>peak</sub>
	External Creepage	7			mm
	External Clearance	7			mm
	Insulation Thickness	0.5			mm
R <sub>IO</sub>	Insulation Resistance at T <sub>S</sub> , V <sub>IO</sub> = 500 V	10 <sup>9</sup>			Ω

#### **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter		Device	Value	Units
Total Devi	ce				l
T <sub>STG</sub>	Storage Temperature		All	-40 to +150	°C
T <sub>OPR</sub>	Operating Temperature		All	-40 to +100	°C
T <sub>SOL</sub>	Lead Solder Temperature		All	260 for 10 sec	°C
P <sub>D</sub>	Total Device Power Dissipation @ T <sub>A</sub> = 25°C		All	250	mW
	Derate Above 25°C			2.94	mW/°C
Emitter					
I <sub>F</sub>	DC/Average Forward Input Current		All	60	mA
V <sub>R</sub>	Reverse Input Voltage		TIL111M	3	V
		МО	C8100M, TIL117M	6	
I <sub>F</sub> (pk)	Forward Current – Peak (300 µs, 2% Duty Cycle)		All	3	Α
$P_{D}$	LED Power Dissipation @ T <sub>A</sub> = 25°C		All	120	mW
	Derate Above 25°C			1.41	mW/°C
Detector	7				
$V_{CEO}$	Collector-Emitter Voltage		All	30	V
V <sub>CBO</sub>	Collector-Base Voltage		All	70	V
V <sub>ECO</sub>	Emitter-Collector Voltage	TI	L111M, TIL117M	7	V
$V_{EBO}$	Emitter-Base Voltage		All	7	
$P_{D}$	Detector Power Dissipation @ T <sub>A</sub> = 25°C		All	150	mW
	Derate Above 25°C			1.76	mW/°C

#### **Electrical Characteristics**

 $T_A = 25$ °C unless otherwise specified.

#### **Individual Component Characteristics**

Symbol	Parameter	Test Conditions		Device	Min.	Тур.*	Max.	Unit
Emitter						•	'	
V <sub>F</sub>			TIL111M		1.2	1.4	V	
	Voltage	$I_F = 10 \text{ mA for}$ $T_A = 0^{\circ}\text{C to } 70^{\circ}\text{C}$		MOC8100M,		1.2	1.4	
		MOC8100M,	T <sub>A</sub> = -55°C	TIL117M		1.32		
		I <sub>F</sub> = 16 mA for TIL117M	T <sub>A</sub> = +100°C			1.10		
I <sub>R</sub>	Reverse Leakage	V <sub>R</sub> = 3.0 V		TIL111M, TIL117M		0.001	10	μΑ
	Current	V <sub>R</sub> = 6.0 V		MOC8100M		0.001	10	μΑ
Detector								
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 1.0 mA, I <sub>F</sub> :	= 0	All	30	100		V
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 10 \mu A, I_F = 0$		All	70	120		V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 10 μA, I <sub>F</sub> = 0		All	7	10		V
BV <sub>ECO</sub>	Emitter-Collector Breakdown Voltage	I <sub>F</sub> = 100 μA, I <sub>F</sub> = 0		TIL111M, TIL117M	7	10		V
I <sub>CEO</sub>	Collector-Emitter	V <sub>CE</sub> = 10 V, I <sub>F</sub> =	: 0	TIL111M, TIL117M		1	50	nA
Dark Current	Dark Current	V <sub>CE</sub> = 5 V, T <sub>A</sub> =	25°C	MOC8100M		0.5	25	nA
		V <sub>CE</sub> = 30 V, I <sub>F</sub> =	: 0, T <sub>A</sub> = 70°C	TIL117M, MOC8100M		0.2	50	μΑ
I <sub>CBO</sub>	Collector-Base Dark	V <sub>CB</sub> = 10 V		TIL111M, TIL117M			20	nA
I <sub>CBO</sub>	Current	V <sub>CB</sub> = 5 V		MOC8100M			10	nA
C <sub>CE</sub>	Capacitance	$V_{CE} = 0 \text{ V, f} = 1$	MHz	All		8		pF

<sup>\*</sup>All Typical values at  $T_A = 25$ °C

#### **Electrical Characteristics** (Continued)

 $T_A = 25$ °C unless otherwise specified.

#### **Transfer Characteristics**

Symbol	Parameter	Test Conditions	Device	Min	Тур*	Max	Unit
DC Chara	cteristics						
CTR <sub>CE</sub>	Current Transfer Ratio, Collector to Emitter	I <sub>F</sub> = 10 mA, V <sub>CE</sub> = 10 V	TIL117M	50			%
		I <sub>F</sub> = 1 mA, V <sub>CE</sub> = 5 V	MOC8100M 50			%	
		I <sub>F</sub> = 1 mA, V <sub>CE</sub> = 5 V, T <sub>A</sub> = 0°C to +70°C		30			
I <sub>C(ON)</sub>	On-State Collector Current (Phototransistor Operation)	I <sub>F</sub> = 16 mA, V <sub>CE</sub> = 0.4 V	TIL111M	2			mA
	On-State Collector Current (Photodiode Operation)	I <sub>F</sub> = 16 mA, V <sub>CB</sub> = 0.4 V		7			μA
CL (SAI)	Collector-Emitter Saturation Voltage	$I_C = 500 \mu A, I_F = 10 mA$	TIL117M			0.4	V
		I <sub>C</sub> = 2 mA, I <sub>F</sub> = 16 mA	TIL111M			0.4	
		I <sub>C</sub> = 100 μA, I <sub>F</sub> = 1 mA	MOC8100M			0.5	
AC Charac	cteristics				•		
c <sub>ON</sub>	Turn-On Time	$I_C = 2 \text{ mA}, V_{CC} = 10 \text{ V},$	MOC8100M			20	μs
		$R_L = 100 \Omega \text{ (Fig. 13)}$	TIL117M			10	
C <sub>OFF</sub>	Turn-Off Time		MOC8100M			20	μs
			TIL117M			10	
t <sub>r</sub>	Rise Time		MOC8100M		2		μs
t <sub>f</sub>	Fall Time		TIL117M		2		
t <sub>r</sub>	Rise Time (Phototransistor Operation)	$I_{C(ON)} = 2 \text{ mA}, V_{CC} = 10 \text{ V},$ $R_L = 100 \Omega \text{ (Fig. 13)}$	TIL111M			10	μs
t <sub>f</sub>	Fall Time (Phototransistor Operation)						

#### **Isolation Characteristics**

Symbol	Characteristic	Test Conditions	Min.	Тур.*	Max.	Units
V <sub>ISO</sub>	Input-Output Isolation Voltage	f = 60 Hz, t = 1 s	7500			V <sub>AC(PK)</sub>
R <sub>ISO</sub>	Isolation Resistance	V <sub>I-O</sub> = 500 V <sub>DC</sub>	10 <sup>11</sup>			Ω
C <sub>ISO</sub>	Isolation Capacitance	$V_{I-O} = 0$ , $f = 1 MHz$		0.2		pF

<sup>\*</sup>All Typical values at  $T_A = 25$ °C.

#### **Typical Performance Characteristics**

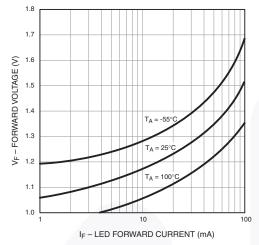


Figure 3. LED Forward Voltage vs. Forward Current

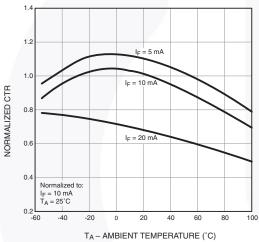


Figure 5. Normalized CTR vs. Ambient Temperature

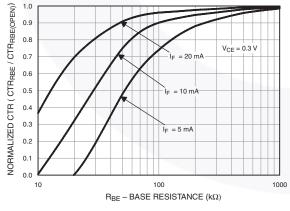


Figure 7. CTR vs. RBE (Saturated)

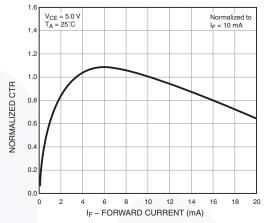


Figure 4. Normalized CTR vs. Forward Current

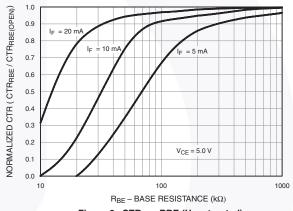


Figure 6. CTR vs. RBE (Unsaturated)

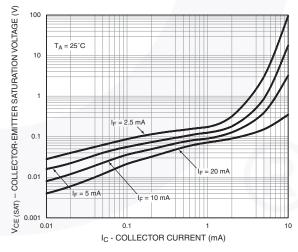


Figure 8. Collector-Emitter Saturation Voltage vs Collector Current

#### **Typical Performance Characteristics** (Continued)

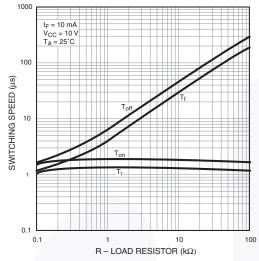


Figure 9. Switching Speed vs. Load Resistor

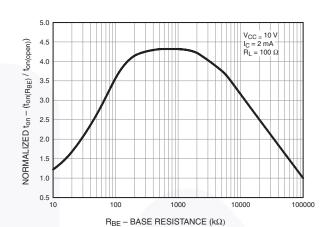
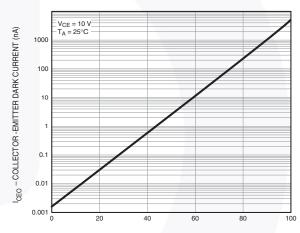


Figure 10. Normalized  $t_{on}$  vs.  $R_{BE}$ 



Figure 11. Normalized toff vs. RBE



 $T_A$  – AMBIENTTEMPERATURE (°C)

Figure 12. Dark Current vs. Ambient Temperature

#### TEST CIRCUIT

# V<sub>CC</sub> = 10 V INPUT OUTPUT Adjust IF to produce Ic = 2 mA

#### WAVEFORMS

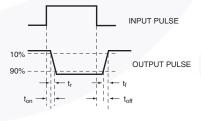


Figure 13. Switching Time Test Circuit and Waveforms



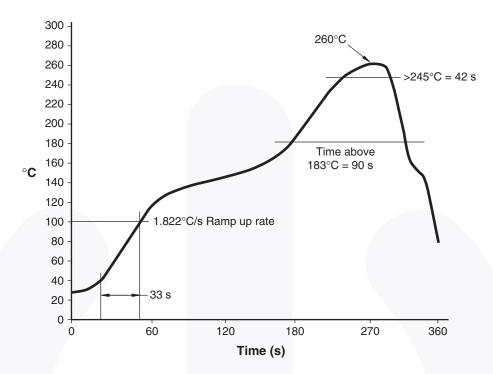
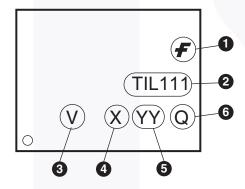


Figure 14. Reflow Profile

#### **Ordering Information**

Option	Order Entry Identifier (Example)	Description
No option	TIL111M	Standard Through-Hole Device
S	TIL111SM	Surface Mount Lead Bend
SR2	TIL111SR2M	Surface Mount; Tape and Reel
Т	TIL111TM	0.4" Lead Spacing
V	TIL111VM	VDE 0884
TV	TIL111TVM	VDE 0884, 0.4" Lead Spacing
SV	TIL111SVM	VDE 0884, Surface Mount
SR2V	TIL111SR2VM	VDE 0884, Surface Mount, Tape and Reel

### **Marking Information**



Definitions					
1	Fairchild logo				
2	Device number				
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)				
4	One-digit year code, e.g., '3'				
5	Two-digit work week ranging from '01' to '53'				
6	Assembly package code				

<sup>\*</sup>Note – Parts that do not have the 'V' option (see definition 3 above) that are marked with date code '325' or earlier are marked in portrait format.

#### **Carrier Tape Specification**

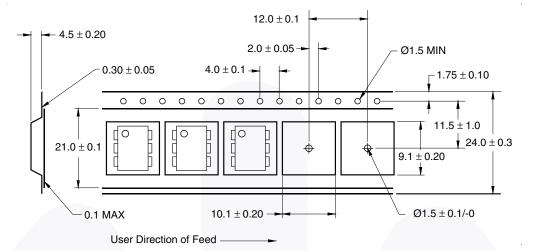
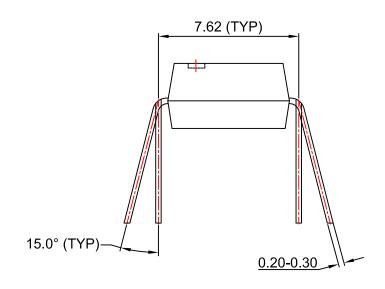
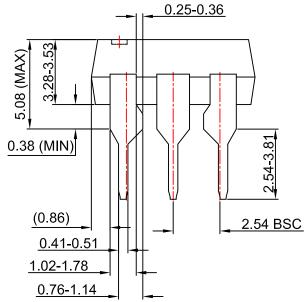


Figure 15. Carrier Tape Specification



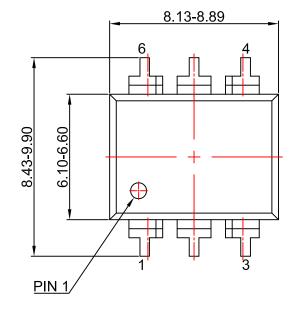


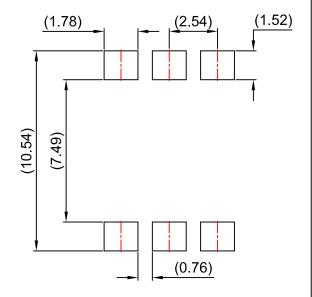


#### NOTES:

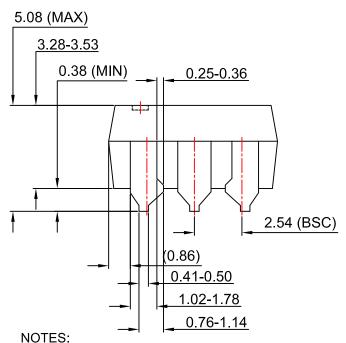
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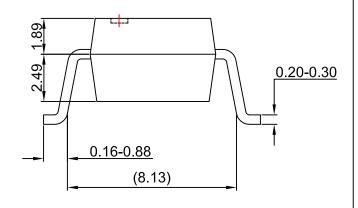






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